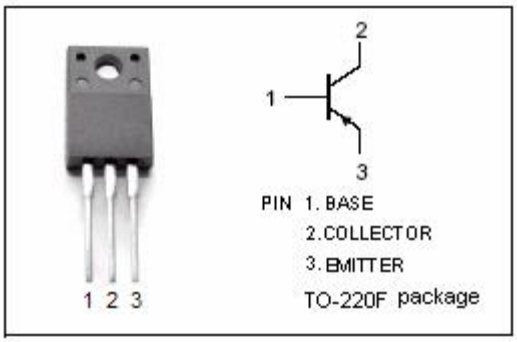
isc Silicon PNP Power Transistor — KSB1097

DESCRIPTION

- High Collector Current:I_C= -7A
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$= -0.5V(Max)@I_C= -5A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

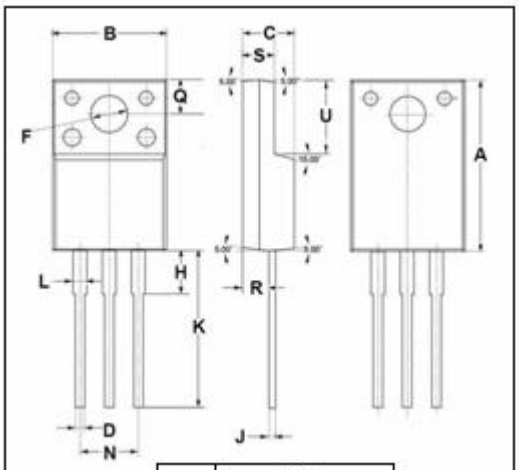


APPLICATIONS

- Designed for low-frequency power amplifiers and low speed switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Pulse	-15	A
I_B	Base Current-Continuous	-3.5	A
P_C	Total Power Dissipation @ T_a=25℃	2	W
	Total Power Dissipation @ T_C=25℃	30	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

isc Silicon PNP Power Transistor KSB1097

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A			-0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μA
h_{FE-1}	DC Current Gain	I_C= -3A; V_{CE}= -1V	40		200	
h_{FE-2}	DC Current Gain	I_C= -5A; V_{CE}= -1V	20			

◆ **h_{FE-1} Classifications**

R	O	Y
40-80	60-120	100-200